



# STMicroelectronics Reveals Latest Power Technology for Greener Industry and Infrastructure

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Advanced internal structure of new power-transistor family delivers industry's best on-state resistance for low-energy, space-efficient designs

Geneva, May 22, 2013 – STMicroelectronics (NYSE: STM), a global semiconductor leader serving customers across the spectrum of electronics applications, has introduced its latest generation of energy-efficient power devices that reduce the environmental impact of equipment such as telecom or computing systems, solar inverters, industrial automation, and automotive applications.

ST's new STripFET™ VII DeepGATE™ MOSFETs deliver the best conducting efficiency among currently available 80V and 100V devices, while switching efficiency is also increased. In addition, the devices help to simplify designs and reduce equipment size and cost by allowing system power and efficiency targets to be met using fewer devices in small package sizes.

The critical advance in ST's STripFET VII DeepGATE technology is an enhanced MOSFET gate structure, which lowers device on-state resistance while also reducing internal capacitances and gate charge for faster, more efficient switching. The devices also have high avalanche ruggedness to survive potentially damaging hard conditions, which makes them a strong choice for automotive applications.

More than 15 STripFET VII DeepGATE devices are available immediately for sample or production orders, including the STP270N8F7 80V device and several 100V parts in a choice of TO-220, DPAK, PowerFLAT™ 5x6, and 2-lead or 6-lead H2PAK packages. Prices for 1000-piece orders range from \$1.70 for the 100V STD100N10F7 and STL100N10F7 to \$3.80 for the STH310N10F7-2 device. If your company has a high-volume need, please contact your ST sales office.

About ST MOSFETs and Voltage Ratings:

STripFET VII DeepGATE joins ST's extensive portfolio of MOSFET technologies offering industry-leading efficiency, power density and ruggedness at key voltage ratings used in various applications. STripFET VII DeepGATE technology is ideal for systems operating at DC voltages such as 48V, which is widely used in telecom applications; devices with 80V or 100V rating have adequate 'safety margin' to withstand typical over-voltage surges in a 48V system. STripFET VII DeepGATE is also chosen for highly rugged performance in 12V or 24V automotive applications.

Other technologies, such as MDmesh™ superjunction technology, are needed for optimum efficiency at higher voltage ratings. 600V or 650V MDmesh devices provide suitable safety margin for applications such as AC/DC power supplies, lighting ballasts and display panels. ST recently announced a new high-efficiency MDmesh family featuring low gate charge for use in resonant converters such as LCD-TV power supplies (MDmesh II Low Qg).

For further information please refer to [www.st.com/pmos](http://www.st.com/pmos)

About STMicroelectronics

ST is a global leader in the semiconductor market serving customers across the spectrum of sense

and power and automotive products and embedded processing solutions. From energy management and savings to trust and data security, from healthcare and wellness to smart consumer devices, in the home, car and office, at work and at play, ST is found everywhere microelectronics make a positive and innovative contribution to people's life. By getting more from technology to get more from life, ST stands for life.augmented.

In 2012, the Company's net revenues were \$8.49 billion. Further information on ST can be found at [www.st.com](http://www.st.com).

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